SEMICONDUCTOR DEVICE BONDING WIRE

Abstract

It is an object of the present invention to provide a copper-based bonding wire in which the material cost is low and ball bondability, reliability in a heat cycle test or reflow test and storage life are excellent and its application is possible for a fine wire used for a fine pitch. The bonding wire includes a core material with copper as its component and an outer layer which is provided on the core material and with difference in component and/or composition from those of the core material. The outer layer is 0.021 to 0.12 μm in thickness.